INTEGRATED CIRCUITS



Product data Supersedes data of 1998 Jan 16

2003 Feb 06





74ABT245

FEATURES

- Octal bidirectional bus interface
- 3-State buffers
- Output capability: +64 mA/-32 mA
- Latch-up protection exceeds 500 mA per Jedec Std 17
- ESD protection exceeds 2000 V per MIL STD 833 Method 3015 and 200 V per Machine Model
- Power-up 3-State
- Live insertion/extraction permitted
- Inputs are disabled during 3-State mode

QUICK REFERENCE DATA

DESCRIPTION

The 74ABT245 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

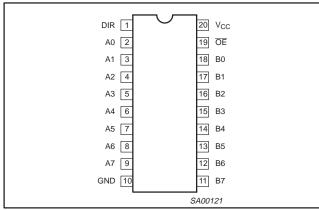
The 74ABT245 device is an octal transceiver featuring non-inverting 3-State bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an Output Enable (\overline{OE}) input for easy cascading and a Direction (DIR) input for direction control.

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25 °C; GND = 0 V	TYPICAL	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	C _L = 50 pF; V _{CC} = 5 V	2.2 2.9	ns
C _{IN}	Input capacitance DIR, OE	$V_{I} = 0 V \text{ or } V_{CC}$	4	pF
C _{I/O}	I/O pin capacitance	Outputs disabled; $V_0 = 0 V$ or V_{CC}	7	pF
I _{CCZ}	Total supply current	Outputs disabled; V _{CC} =5.5 V	50	μA

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	PART NUMBER	DWG NUMBER
20-Pin plastic SO	–40 °C to +85 °C	74ABT245D	SOT163-1
20-Pin Plastic SSOP Type II	–40 °C to +85 °C	74ABT245DB	SOT339-1
20-Pin Plastic TSSOP Type I	–40 °C to +85 °C	74ABT245PW	SOT360-1

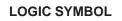
PIN CONFIGURATION

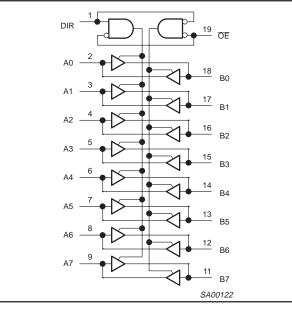


PIN DESCRIPTION

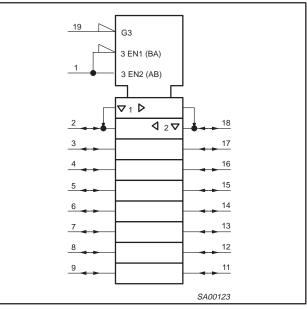
PIN NUMBER	SYMBOL	NAME AND FUNCTION
1	DIR	Direction control input
2, 3, 4, 5, 6, 7, 8, 9	A0 – A7	Data inputs/outputs (A side)
18, 17, 16, 15, 14, 13, 12, 11	B0 – B7	Data inputs/outputs (B side)
19	ŌĒ	Output enable input (active-LOW)
10	GND	Ground (0 V)
20	V _{CC}	Positive supply voltage

74ABT245





LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INP	JTS	INPUTS/C	OUTPUTS
ŌĒ	DIR	An	Bn
L	L	An = Bn	Inputs
L	Н	Inputs	Bn = An
н	Х	Z	Z

H = High voltage level

L = Low voltage level

X = Don't care Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current	V ₁ < 0	-18	mA
VI	DC input voltage ³		-1.2 to +7.0	V
I _{ОК}	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I _{OUT}	DC output current	output in Low state	128	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	UNIT	
STMBOL	PARAMEIER	Min	Max	UNIT
V _{CC}	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V _{CC}	V
V _{IH}	HIGH-level input voltage	2.0		V
V _{IL}	LOW-level Input voltage		0.8	V
I _{OH}	HIGH-level output current		-32	mA
I _{OL}	LOW-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	5	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS

				LIMITS					
SYMBOL	PARAMETER		TEST CONDITIONS		T _{amb} = +25 °C			T _{amb} = −40 °C to +85 °C	
				Min	Тур	Max	Min	Max	
V _{IK}	Input clamp volt	age	V _{CC} = 4.5 V; I _{IK} = -18 mA		-0.9	-1.2		-1.2	V
	1		V_{CC} = 4.5 V; I_{OH} = -3 mA; V_I = V_{IL} or V_{IH}	2.5	2.9		2.5		V
V _{OH}	High-level outpu	ut voltage	V_{CC} = 5.0 V; I_{OH} = -3 mA; V_I = V_{IL} or V_{IH}	3.0	3.4		3.0		V
			V_{CC} = 4.5 V; I_{OH} = –32 mA; V_{I} = V_{IL} or V_{IH}	2.0	2.4		2.0		V
V _{OL}	Low-level output	t voltage	V_{CC} = 4.5 V; I _{OL} = 64 mA; V _I = V _{IL} or V _{IH}		0.42	0.55		0.55	V
	Input leakage	Control pins	V_{CC} = 5.5 V; V_{I} = GND or 5.5 V		±0.01	±1.0		±1.0	μA
li li	current	Data pins	V_{CC} = 5.5 V; V_{I} = GND or 5.5 V		±5	±100		±100	μΑ
I _{OFF}	Power-off leakage current		V_{CC} = 0.0 V; V _I or V _O \leq 4.5 V		±5.0	±100		±100	μΑ
I _{PU} /I _{PD}	Power-up/down 3-State output current ³		V_{CC} = 2.0 V; V_{O} = 0.5 V; V_{I} = GND or V_{CC} ; V_{OE} = Don't care		±5.0	±50		±50	μΑ
I _{IH} + I _{OZH}	3-State output H	ligh current	V_{CC} = 5.5 V; V_{O} = 2.7 V; V_{I} = V_{IL} or V_{IH}		5.0	50		50	μA
I _{IL} + I _{OZL}	3-State output L	ow current	V_{CC} = 5.5 V; V_{O} = 0.5 V; V_{I} = V_{IL} or V_{IH}		-5.0	-50		-50	μΑ
I _{CEX}	Output high leal	kage current	V_{CC} = 5.5 V; V_{O} = 5.5 V; V_{I} = GND or V_{CC}		5.0	50		50	μΑ
Ι _Ο	Output current ¹		V_{CC} = 5.5 V; V_{O} = 2.5 V	-40	-100	-180	-40	-180	mA
I _{ССН}			V_{CC} = 5.5 V; Outputs HIGH; V _I = GND or V _{CC}		50	250		250	μA
I _{CCL}	Quiescent supp	ly current	V_{CC} = 5.5 V; Outputs LOW; V _I = GND or V _{CC}		24	30		30	mA
I _{CCZ}			V_{CC} = 5.5 V; Outputs 3-State; V _I = GND or V _{CC}		50	250		250	μΑ
			Outputs enabled, one input at 3.4 V, other inputs at V _{CC} or GND; V _{CC} = 5.5 V		0.5	1.5		1.5	mA
ΔI_{CC}	Additional supplinput pin ²	y current per	Outputs 3-State, one data input at 3.4 V, other inputs at V _{CC} or GND; V _{CC} = 5.5 V		50	250		250	μΑ
			Outputs 3-State, one enable input at 3.4 V, other inputs at V _{CC} or GND; V _{CC} = 5.5 V		0.5	1.5		1.5	mA

NOTES:

1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

This is the increase in supply current for each input at 3.4 V.
 This parameter is valid for any V_{CC} between 0 V and 2.1 V with a transition time of up to 10 msec. For V_{CC} = 2.1 V to V_{CC} = 5 V±10%, a transition time of up to 100 μsec is permitted.

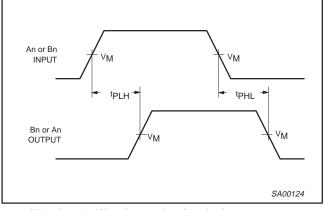
AC CHARACTERISTICS

GND = 0 V; $t_R = t_F$ = 2.5 ns; C_L = 50 pF, R_L = 500 Ω

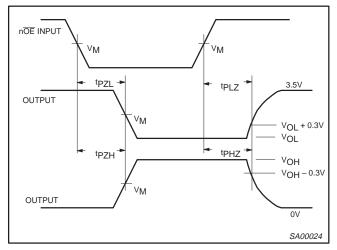
					LIMI	ſS		
SYMBOL	PARAMETER	WAVEFORM	T _{amb} = +25 °C V _{CC} = +5.0 V			$\begin{array}{l} T_{amb} = -40 \ ^\circ C \ to \ +85 \ ^\circ C \\ V_{CC} = +5.0 \ V \ \pm 0.5 \ V \end{array}$		UNIT
			Min	Тур	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	1	1.0 1.0	2.2 2.9	4.1 4.2	1.0 1.0	4.6 4.6	ns
t _{PZH} t _{PZL}	Output enable time to HIGH and LOW level	2	1.3 2.3	3.0 4.0	4.8 5.8	1.3 2.3	5.3 6.3	ns
t _{PHZ} t _{PLZ}	Output disable time from HIGH and LOW Level	2	1.0 1.0	4.7 4.1	6.2 5.8	1.0 1.0	7.2 6.3	ns

AC WAVEFORMS

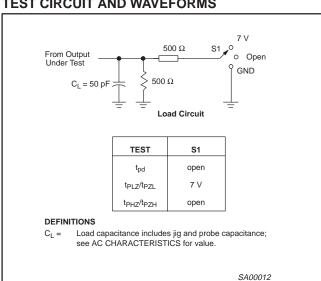
 $V_M = 1.5V$, $V_{IN} = GND$ to 3.0V



Waveform 1. Waveforms showing the input to output propagation delays

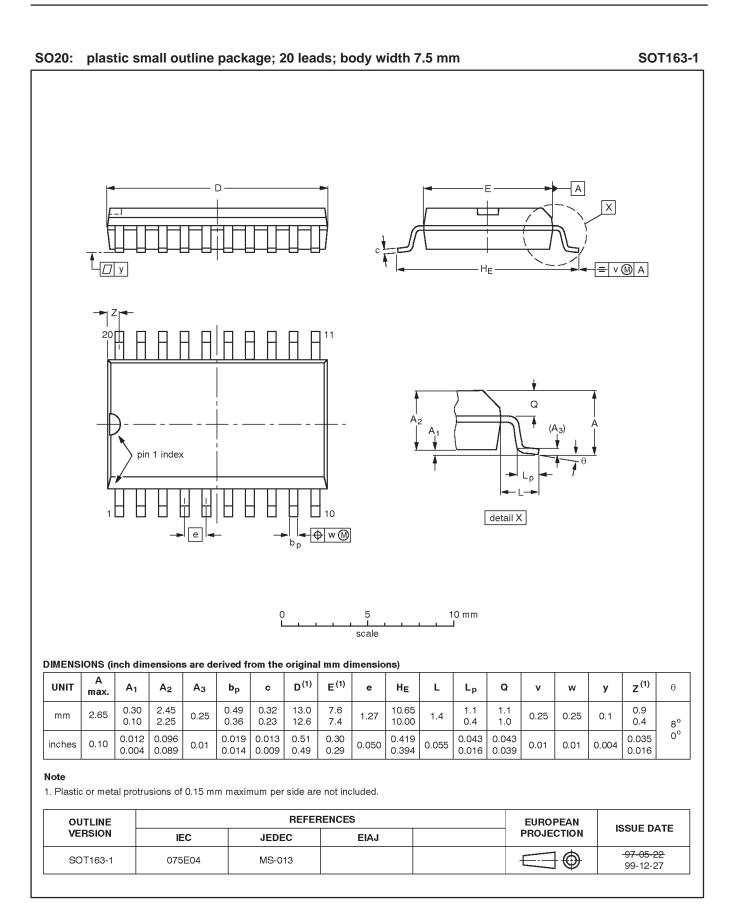


Waveform 2. Waveforms showing the 3-State Output Enable and Disable times

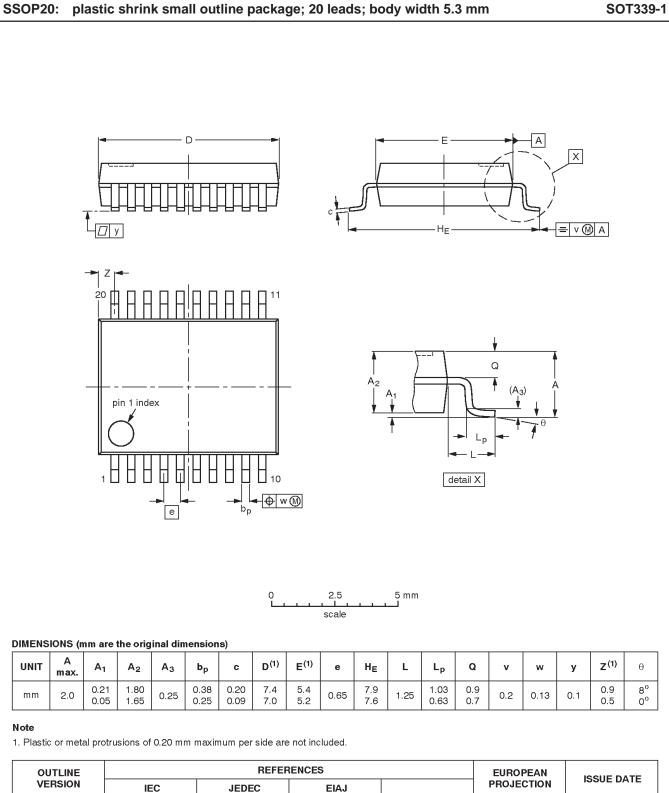


TEST CIRCUIT AND WAVEFORMS

Product data







SOT339-1

MO-150

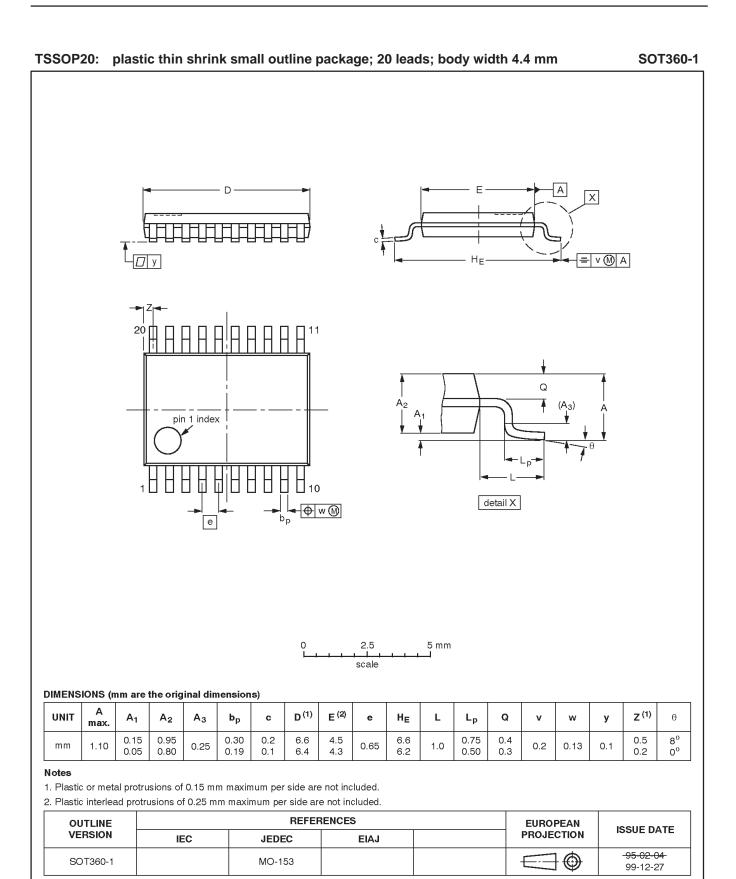
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REVISION HISTORY

Rev	Date	Description
_3	20030206	Product data (9397 750 11087); ECN 853-1447 29305 of 17 December 2002; Supersedes Product specfication (9397 750 03467) of 1998 Jan 16. Modifications:
		 Delete all references to N package. DIP20 package option discontinued.
_2	19980116	Product specification (9397 750 03467) 1998 Jan 16; ECN 853-1447 18867 of 16 January 1998. Supersedes data of 1996 Sep 10.

Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definitions
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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